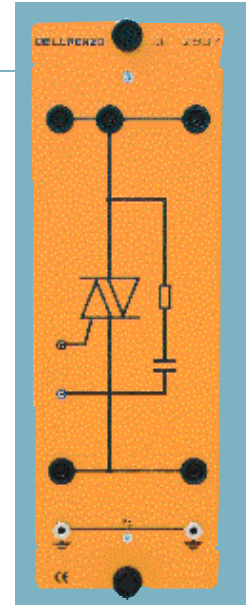


**DL 2605
GROUP OF SCR**
Six silicon controlled rectifiers with RCD protection network used for realizing controlled rectifiers and inverters.

Technical features:
Direct average current
 $I_{TAV} = 7.6 \text{ A max.}$
True rms value of the direct current
 $I_{TRMS} = 12 \text{ A}$

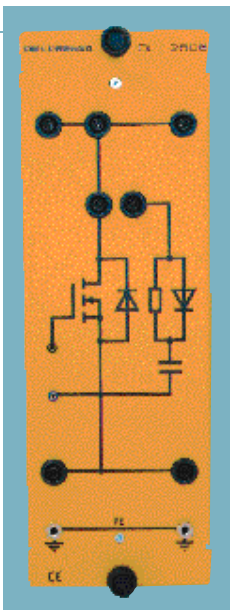
Max. repetitive reverse voltage $U_{RRM} = 800 \text{ V}$
Trigger current $I_{GT} = 15 \text{ mA max.}$
Trigger voltage $U_{GT} = 1.5 \text{ V max.}$
 $I^2t = 72 \text{ A}^2\text{s}$



**DL 2607
TRIAC**
Bidirectional thyristor used for the control in alternated current. Complete with RC suppressor network.

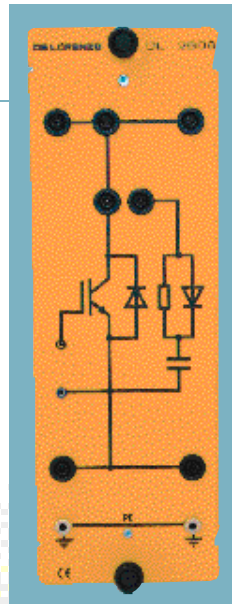
Technical features:
True rms value of the direct current $I_{TRMS} = 8 \text{ A}$

Non-repetitive peak current
 $I_{TSM} = 70 \text{ A, } 50 \text{ Hz (77 A, } 60 \text{ Hz)}$
Max. repetitive reverse voltage
 $U_{DRM} = 800 \text{ V}$
Trigger current $I_{GT} = 25 \text{ mA max.}$
(all the quadrants)
Trigger voltage $U_{GT} = 2.5 \text{ V max.}$
State keeping current
 $I_H = 25 \text{ mA max.}$
 $I^2t = 24 \text{ A}^2\text{s}$



**DL 2608
MOSFET**
N-channel enhancement mode power MOS with integrated reverse diode (FRED, Fast Recovery Epitaxial Diode) used as very fast switch in switching regulators and inverters.

Technical features
Drain-source voltage $U_{DS} = 400 \text{ V}$
Continuous drain current
 $I_D = 10 \text{ A}$
Drain-source on-state resistance
 $R_{DS(on)} = 0.55$
Gate-source voltage $U_{GS} = \pm 20 \text{ V}$



**DL 2609
IGBT**
N-channel Insulated Gate Bipolar Transistor (IGBT) with anti-parallel hyperfast protection diode used as very fast switch in switching regulators and inverters.

Technical features
Collector-emitter voltage
 $U_{CES} = 600 \text{ V}$
Continuous collector current
 $I_C = 24 \text{ A at } T_C = 25 \text{ }^\circ\text{C}$
Collector-emitter saturation voltage $U_{CESat} = 1.8 \text{ V}_{typ}$ at $I_C = 15$

A
Gate-emitter voltage $U_{GE} = \pm 20 \text{ V}$